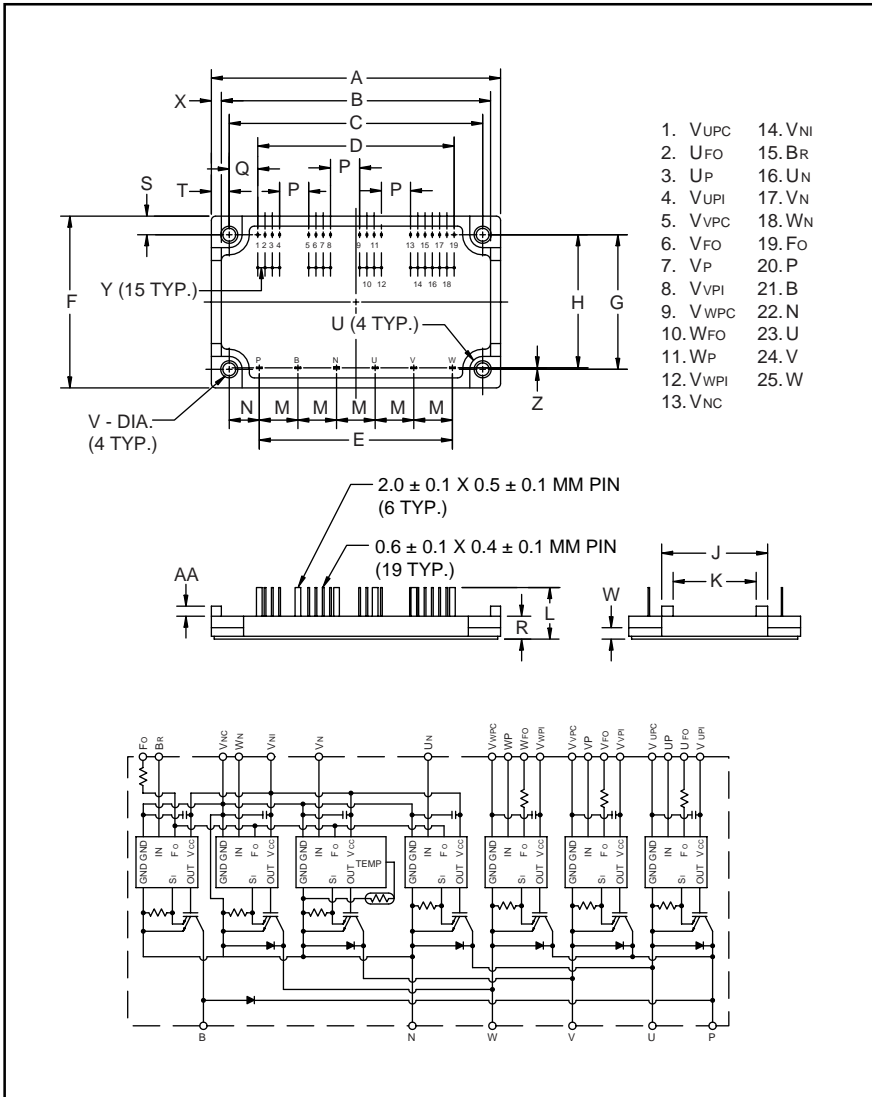


# PM10RSH120

FLAT-BASE TYPE  
INSULATED PACKAGE



- |                      |                     |
|----------------------|---------------------|
| 1. V <sub>UPC</sub>  | 14. V <sub>NI</sub> |
| 2. U <sub>FO</sub>   | 15. BR              |
| 3. U <sub>P</sub>    | 16. U <sub>N</sub>  |
| 4. V <sub>UPI</sub>  | 17. V <sub>N</sub>  |
| 5. V <sub>VPC</sub>  | 18. W <sub>N</sub>  |
| 6. V <sub>FO</sub>   | 19. FO              |
| 7. V <sub>P</sub>    | 20. P               |
| 8. V <sub>VPI</sub>  | 21. B               |
| 9. V <sub>WPC</sub>  | 22. N               |
| 10. W <sub>FO</sub>  | 23. U               |
| 11. W <sub>P</sub>   | 24. V               |
| 12. V <sub>VPI</sub> | 25. W               |
| 13. V <sub>NC</sub>  |                     |



**Description:**

Mitsubishi Intelligent Power Modules are isolated base modules designed for power switching applications operating at frequencies to 20kHz. Built-in control circuits provide optimum gate drive and protection for the IGBT and free-wheel diode power devices.

**Features:**

- Complete Output Power Circuit
- Gate Drive Circuit
- Protection Logic
  - Short Circuit
  - Over Current
  - Over Temperature
  - Under Voltage

**Applications:**

- Inverters
- UPS
- Motion/Servo Control
- Power Supplies

**Ordering Information:**

Example: Select the complete part number from the table below -i.e. PM10RSH120 is a 1200V, 10 Ampere Intelligent Power Module.

Type	Current Rating Amperes	V <sub>CES</sub> Volts (x 10)
PM	10	120

**Outline Drawing and Circuit Diagram**

Dimensions	Inches	Millimeters
A	3.98±0.04	101.0±1.0
B	3.78	96.0
C	3.48±0.03	88.5±0.8
D	2.700±0.03	68.58±0.8
E	2.66±0.02	67.5±0.5
F	2.36±0.04	60.0±1.0
G	1.85±0.02	47.0±0.5
H	1.83±0.03	46.5±0.8
J	1.28	32.6
K	0.97	24.6
L	0.71±0.04	18.0±1.0
M	0.53±0.01	13.5±0.3

Dimensions	Inches	Millimeters
N	0.41	10.5
P	0.400	10.16
Q	0.392	9.96
R	0.31	8.0
S	0.26	6.5
T	0.246	6.25
U	0.18 Rad.	Rad. 4.5
V	0.18 Dia.	Dia. 4.5
W	0.17±0.02	4.4±0.5
X	0.10	2.5
Y	0.100±0.01	2.54±0.25
Z	0.02	0.5
AA	0.14	3.5

**PM10RSH120**FLAT-BASE TYPE  
INSULATED PACKAGE**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Ratings	Symbol	PM10RSH120	Units
Power Device Junction Temperature	$T_j$	-20 to 150	$^\circ\text{C}$
Storage Temperature	$T_{\text{stg}}$	-40 to 125	$^\circ\text{C}$
Case Operating Temperature	$T_C$	-20 to 100	$^\circ\text{C}$
Mounting Torque, M4 Mounting Screws	—	0.98 ~ 1.47	N · m
Module Weight (Typical)	—	100	Grams
Supply Voltage Protected by OC and SC ( $V_D = 13.5 - 16.5\text{V}$ , Inverter Part, $T_j = 125^\circ\text{C}$ )	$V_{\text{CC(prot.)}}$	800	Volts
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{\text{iso}}$	2500	Vrms

**Control Sector**

Supply Voltage (Applied between $V_{\text{UP1}}-V_{\text{UPC}}$ , $V_{\text{VP1}}-V_{\text{VPC}}$ , $V_{\text{WP1}}-V_{\text{WPC}}$ , $V_{\text{N1}}-V_{\text{NC}}$ )	$V_D$	20	Volts
Input Voltage (Applied between $U_P-V_{\text{UPC}}$ , $V_P-V_{\text{VPC}}$ , $W_P-V_{\text{WPC}}$ , $U_N \cdot V_N \cdot W_N \cdot B_r-V_{\text{NC}}$ )	$V_{\text{CIN}}$	20	Volts
Fault Output Supply Voltage Applied between ( $U_{\text{FO}}-V_{\text{UPC}}$ , $V_{\text{FO}}-V_{\text{VPC}}$ , $W_{\text{FO}}-V_{\text{WPC}}$ , $F_O-V_{\text{NC}}$ )	$V_{\text{FO}}$	20	Volts
Fault Output Current (Sink Current at $U_{\text{FO}}$ , $V_{\text{FO}}$ , $W_{\text{FO}}$ and $F_O$ Terminal)	$I_{\text{FO}}$	20	mA

**IGBT Inverter Sector**

Collector-Emitter Voltage ( $V_D = 15\text{V}$ , $V_{\text{CIN}} = 15\text{V}$ )	$V_{\text{CES}}$	1200	Volts
Collector Current, ( $T_C = 25^\circ\text{C}$ )	$I_C$	10	Amperes
Peak Collector Current, ( $T_C = 25^\circ\text{C}$ )	$I_{\text{CP}}$	20	Amperes
Supply Voltage (Applied between P - N)	$V_{\text{CC}}$	900	Volts
Supply Voltage, Surge (Applied between P - N)	$V_{\text{CC(surge)}}$	1000	Volts
Collector Dissipation	$P_C$	62	Watts

**Brake Sector**

Collector-Emitter Voltage ( $V_D = 15\text{V}$ , $V_{\text{CIN}} = 15\text{V}$ )	$V_{\text{CES}}$	1200	Volts
Collector Current, ( $T_C = 25^\circ\text{C}$ )	$I_C$	10	Amperes
Peak Collector Current, ( $T_C = 25^\circ\text{C}$ )	$I_{\text{CP}}$	20	Amperes
Supply Voltage (Applied between P - N)	$V_{\text{CC}}$	900	Volts
Supply Voltage, Surge (Applied between P - N)	$V_{\text{CC(surge)}}$	1000	Volts
Collector Dissipation	$P_C$	41	Watts
Diode Forward Current	$I_F$	10	Amperes
Diode DC Reverse Voltage	$V_{\text{R(DC)}}$	1200	Volts

# PM10RSH120

FLAT-BASE TYPE  
INSULATED PACKAGE

## Electrical and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
<b>Control Sector</b>						
Over Current Trip Level Inverter Part	OC	$-20^\circ\text{C} \leq T \leq 125^\circ\text{C}$ , $V_D = 15\text{V}$	15	27	—	Amperes
Over Current Trip Level Brake Part			15	27	—	Amperes
Short Circuit Trip Level Inverter Part	SC	$-20^\circ\text{C} \leq T \leq 125^\circ\text{C}$ , $V_D = 15\text{V}$	—	41	—	Amperes
Short Circuit Trip Level Brake Part			—	41	—	Amperes
Over Current Delay Time	$t_{\text{off(OC)}}$	$V_D = 15\text{V}$	—	10	—	$\mu\text{s}$
Over Temperature Protection	OT	Trip Level	100	110	125	$^\circ\text{C}$
	$OT_r$	Reset Level	—	90	—	$^\circ\text{C}$
Supply Circuit Under Voltage Protection	UV	Trip Level	11.5	12.0	12.5	Volts
	$UV_r$	Reset Level	—	12.5	—	Volts
Supply Voltage	$V_D$	Applied between $V_{UP1}-V_{UPC}$ , $V_{VP1}-V_{VPC}$ , $V_{WP1}-V_{WPC}$ , $V_{N1}-V_{NC}$	13.5	15	16.5	Volts
Circuit Current	$I_D$	$V_D = 15\text{V}$ , $V_{CIN} = 15\text{V}$ , $V_{N1}-V_{NC}$	—	25	35	mA
		$V_D = 15\text{V}$ , $V_{CIN} = 15\text{V}$ , $V_{XP1}-V_{XPC}$	—	7	10	mA
Input ON Threshold Voltage	$V_{\text{th(on)}}$	Applied between	1.2	1.5	1.8	Volts
Input OFF Threshold Voltage	$V_{\text{th(off)}}$	$U_P-V_{UPC}$ , $V_P-V_{VPC}$ , $W_P-V_{WPC}$ , $U_N \cdot V_N \cdot W_N \cdot B_r-V_{NC}$	1.7	2.0	2.3	Volts
PWM Input Frequency	$f_{\text{PWM}}$	3- $\phi$ Sinusoidal	—	15	20	kHz
Fault Output Current	$I_{\text{FO(H)}}$	$V_D = 15\text{V}$ , $V_{\text{FO}} = 15\text{V}$	—	—	0.01	mA
	$I_{\text{FO(L)}}$	$V_D = 15\text{V}$ , $V_{\text{FO}} = 15\text{V}$	—	10	15	mA
Minimum Fault Output Pulse Width	$t_{\text{FO}}$	$V_D = 15\text{V}$	1.0	1.8	—	ms

# PM10RSH120

FLAT-BASE TYPE  
INSULATED PACKAGE

## Electrical and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
<b>IGBT Inverter Sector</b>						
Collector Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, T_j = 25^\circ\text{C}$	—	—	1.0	mA
		$V_{CE} = V_{CES}, T_j = 125^\circ\text{C}$	—	—	10	mA
Emitter-Collector Voltage	$V_{EC}$	$-I_C = 10\text{A}, V_D = 15\text{V}, V_{CIN} = 5\text{V}$	—	2.5	3.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_D = 15\text{V}, V_{CIN} = 0\text{V}, I_C = 10\text{A}$	—	2.3	3.3	Volts
		$V_D = 15\text{V}, V_{CIN} = 0\text{V}, I_C = 10\text{A}, T_j = 125^\circ\text{C}$	—	2.1	3.1	Volts
Inductive Load Switching Times	$t_{on}$		0.4	0.7	1.5	$\mu\text{s}$
	$t_{rr}$	$V_D = 15\text{V}, V_{CIN} = 0\text{V} \leftrightarrow 15\text{V}$	—	0.15	0.3	$\mu\text{s}$
	$t_{C(on)}$	$V_{CC} = 600\text{V}, I_C = 10\text{A}$	—	0.3	1.0	$\mu\text{s}$
	$t_{off}$	$T_j = 125^\circ\text{C}$	—	1.7	2.9	$\mu\text{s}$
	$t_{C(off)}$		—	0.6	1.2	$\mu\text{s}$
<b>Brake Sector</b>						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$ $T_j = 25^\circ\text{C}$	$V_D = 15\text{V}, V_{CIN} = 0\text{V}, I_C = 10\text{A},$	—	2.8	3.8	Volts
		$V_D = 15\text{V}, V_{CIN} = 0\text{V}, I_C = 10\text{A}, T_j = 125^\circ\text{C}$	—	2.5	3.5	Volts
Diode Forward Voltage	$V_{FM}$	$I_F = 10\text{A}, V_D = 15\text{V}, V_{CIN} = 5\text{V}$	—	2.5	3.5	Volts
Collector Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}, T_j = 25^\circ\text{C}$	—	—	1	mA
		$V_{CE} = V_{CES}, T_j = 125^\circ\text{C}$	—	—	10	mA

# PM10RSH120

FLAT-BASE TYPE  
INSULATED PACKAGE

## Thermal Characteristics

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Units
Junction to Case Thermal Resistance	$R_{th(j-c)Q}$	Each Inverter IGBT	—	—	2.0	°C/Watt
	$R_{th(j-c)F}$	Each Inverter FWDi	—	—	5.5	°C/Watt
	$R_{th(c-f)Q}$	Each Brake IGBT	—	—	3.0	°C/Watt
	$R_{th(c-f)F}$	Each Brake FWDi	—	—	5.5	°C/Watt
Contact Thermal Resistance	$R_{th(c-f)}$	Case to Fin Per Module, Thermal Grease Applied	—	—	0.044	°C/Watt

## Recommended Conditions for Use

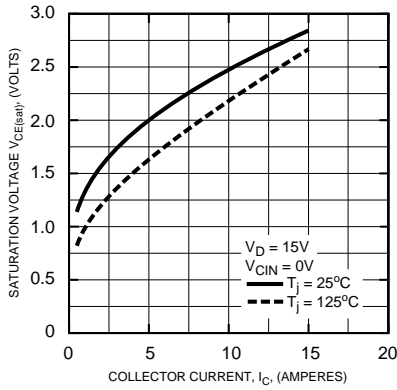
Characteristic	Symbol	Condition	Value	Units
Supply Voltage	$V_{CC}$	Applied across P-N Terminals	0 ~ 800	Volts
	$V_D$	Applied between $V_{UP1}$ - $V_{UPC}$ , $V_{N1}$ - $V_{NC}$ , $V_{VP1}$ - $V_{VPC}$ , $V_{WP1}$ - $V_{WPC}$	$15 \pm 1.5$	Volts
Input ON Voltage	$V_{CIN(on)}$	Applied between	0 ~ 0.8	Volts
Input OFF Voltage	$V_{CIN(off)}$	$U_P, V_P, W_P, U_N, V_N, W_N, B_r$	$4.0 \sim V_D$	Volts
PWM Input Frequency	$f_{PWM}$	Using Application Circuit	5 ~ 20	kHz
Minimum Dead Time	$t_{dead}$	Input Signal	$\geq 2.5$	$\mu s$

# PM10RSH120

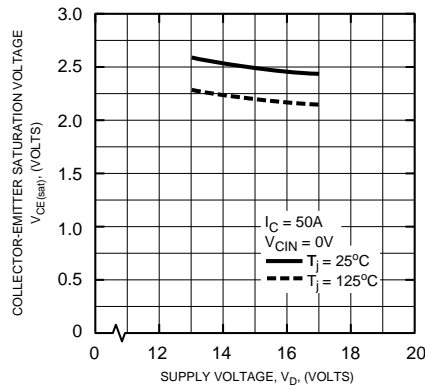
FLAT-BASE TYPE  
INSULATED PACKAGE

## Inverter Part

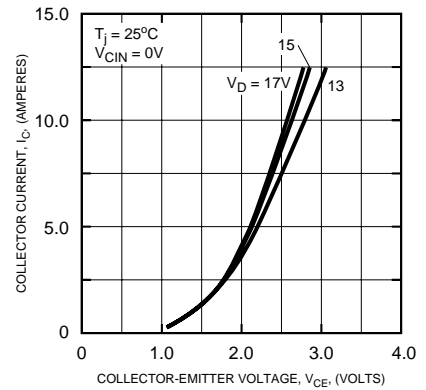
**SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



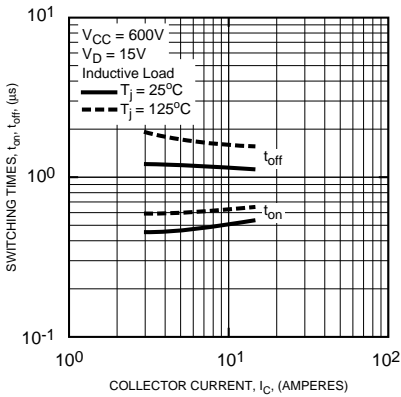
**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



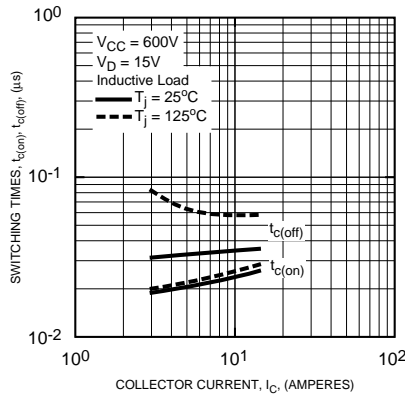
**OUTPUT CHARACTERISTICS (TYPICAL)**



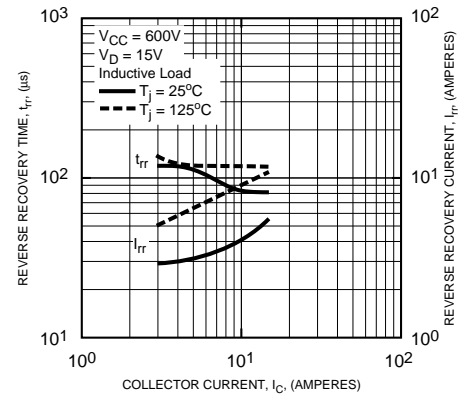
**SWITCHING TIME VS. COLLECTOR CURRENT (TYPICAL)**



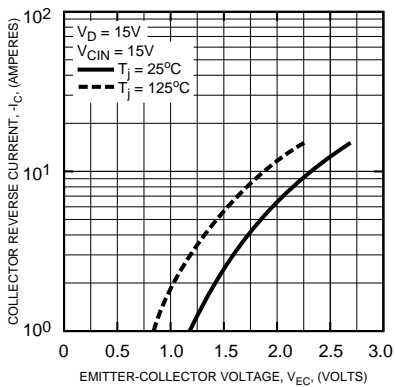
**SWITCHING TIME VS. COLLECTOR CURRENT (TYPICAL)**



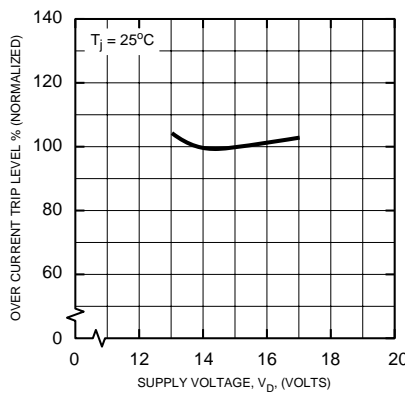
**REVERSE RECOVERY CURRENT VS. COLLECTOR CURRENT (TYPICAL)**



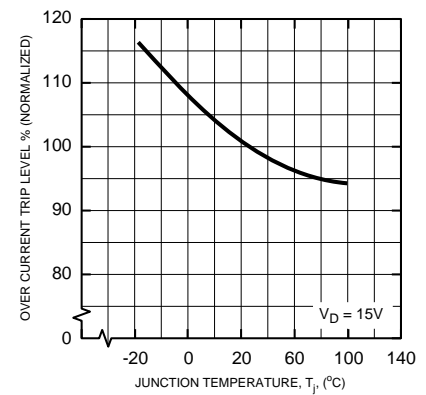
**DIODE FORWARD CHARACTERISTICS**



**OVER CURRENT TRIP LEVEL VS. SUPPLY VOLTAGE (TYPICAL)**



**OVER CURRENT TRIP LEVEL VS. TEMPERATURE (TYPICAL)**

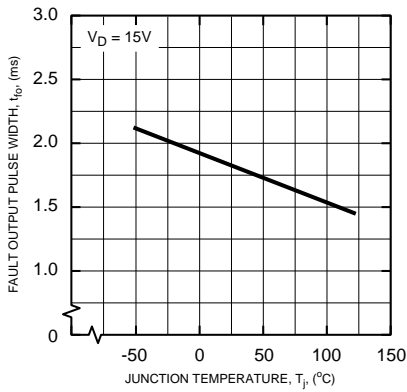


# PM10RSH120

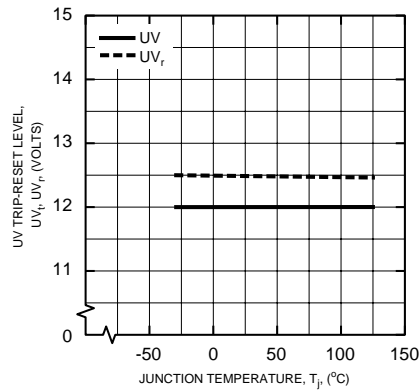
FLAT-BASE TYPE  
INSULATED PACKAGE

## Inverter Part

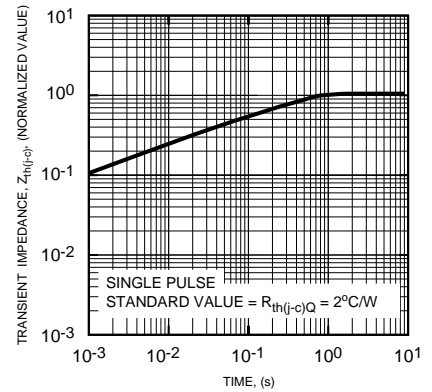
FAULT OUTPUT PULSE WIDTH VS. TEMPERATURE (TYPICAL)



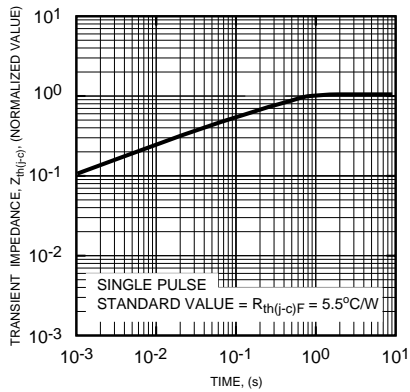
CONTROL SUPPLY VOLTAGE TRIP-RESET LEVEL TEMPERATURE DEPENDENCY (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (Each IGBT)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (Each FWDi)

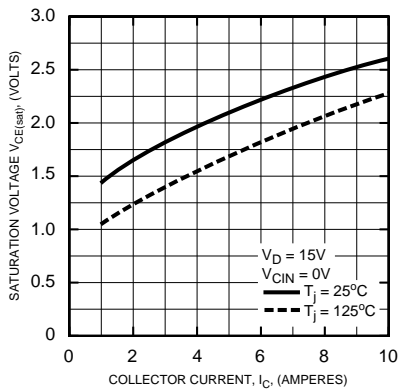


# PM10RSH120

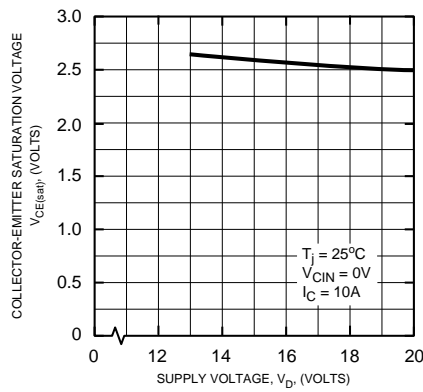
FLAT-BASE TYPE  
INSULATED PACKAGE

## Brake Part

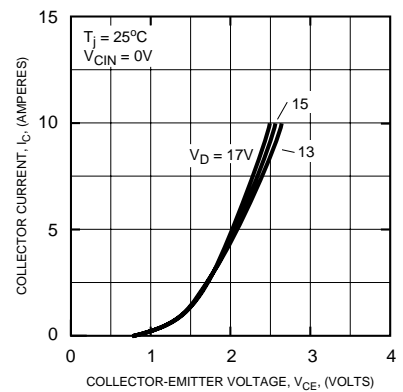
SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



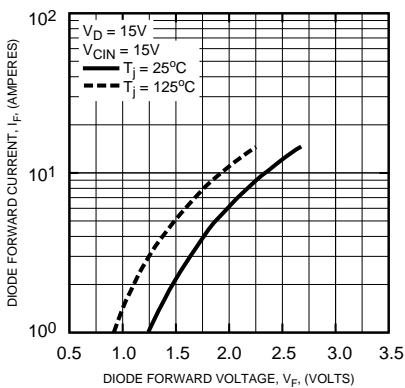
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



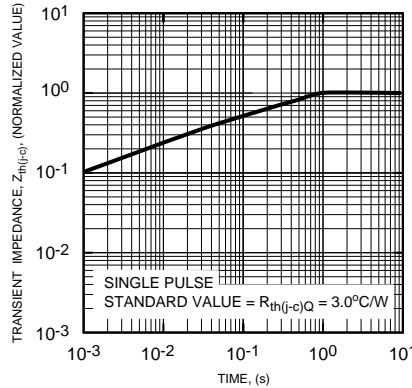
OUTPUT CHARACTERISTICS (TYPICAL)



DIODE FORWARD CHARACTERISTICS



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (Each IGBT)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (Each FWDi)

